

## Mid-Semester Exam

Date: FN/AN Spring Semester - 2017-2018 Subject no. <u>EC 21008</u>

Time: 2 hours; Full Marks: 90 Department: <u>E & ECE</u>

Number of Students: 260

II year B. Tech. Subject name: Analog Electronic Circuits

## Instruction:

1. Answers of all parts of a question must be at one place.

2. Wherever it is necessary, you may use assumption(s) with reasonable justification

3. Assume BJTs are in active mode and MOSFETs are in saturation for the circuits where numerical values of bias voltage and currents are not given.

4. For BJTs Unless otherwise stated use,  $|V_{BE(on)}|\approx 0.6V$ ,  $|V_{CE(sat)}|=0.3V$ ,  $V_A=100V$ , and

5. For NMOS and PMOS, unless otherwise stated, assume  $\mu_n C_{ox}$  = 200  $\mu A/V^2$ ,  $\mu_p C_{ox}$  = 100  $\mu A/V^2$ , and  $V_{TH}$  = 0.4 V for NMOS devices and -0.4 V for PMOS devices.

1. Determine the region of operation of  $M_1$  of the following circuits in Fig. 1: [1+1+1=3 Marks]

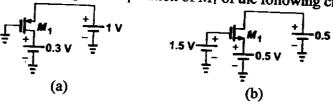


Fig. 1

2. Answer the following multiple-choice questions:

(a) The small-signal resistance (i.e.,  $dV_B/dI_D$ ) in  $k\Omega$  offered by the n-channel MOSFET, M, shown in Fig. 2, at a bias point of  $V_B=2$  V is (device data for M:  $\mu_n C_{ox}(W/L) =$ 80  $\mu AV^2$ , threshold voltage  $V_{TN} = 1$  V, and neglect channel length modulation),

6.25

ii. 25

iii. 12.5

(b) Consider the circuit in Fig. 3, where  $v_1$  represents the signal generated by a microphone,  $I_S = 6 \times 10^{-16} A, \beta =$ 100, and  $V_A = 50 V$ . Obtain the small signal parameters of the transistor  $Q_1$ .

i.  $g_m = 0.53$  mho,  $r_\pi = 188 \,\Omega$ , and  $r_o = 3.6 \,k\Omega$ 

ii.  $g_m = 0.32$  mho,  $r_\pi = 188$   $\Omega$ , and  $r_o = 3.6$   $k\Omega$ 

iii.  $g_m=0.53$  mho,  $r_\pi=377$   $\Omega$ , and  $r_o=5.6$   $k\Omega$ 

iv.  $g_m = 5.3$  mho,  $r_\pi = 37.7~\Omega$ , and  $r_o = 4.34~M\Omega$ 

(c) Among the 4 options given below, select the correct value of W/L of  $M_1$  in Fig. 4 that places  $M_1$  at the edge-ofsaturation  $\mu_n C_{ox} = 100 \mu A/V^2$  and  $V_{TH} = 0.5 \text{V}$ ?

i. 4.8/0.18

ii. 4.0/0.18

iii. 7.48/0.18

iv. 5.48/0.18

$$1 \sqrt{\frac{+}{L^{-}}} + \sqrt{\frac{+}{L^{-}}} 0.9 \sqrt{\frac{+}{L^{-}}} = 0.9 \sqrt{\frac{+}{L^{L$$

$$[1+3+1=5 Marks]$$



Fig. 2

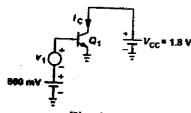


Fig. 3

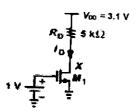
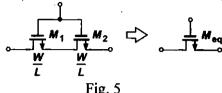


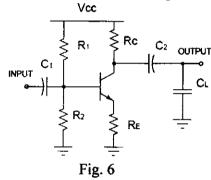
Fig. 4

3. Two identical MOSFETs are placed in series as shown in Fig. 5. If both devices operate as resistors, prove that the combination behaves as a single transistor,  $M_{eq}$ . Obtain the ratio of width and length of  $M_{eq}$  in terms of W/L. (Hint: Write expression of resistance of  $M_1$  and  $M_2$  as  $R_1$  and  $R_2$ , respectively and then find the series resistance.)

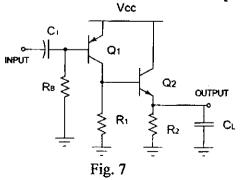
[4 Marks]



4. A common emitter (CE) amplifier circuit is shown in Fig. 6. Given values of the circuit components are: R1 = 18.8 k $\Omega$ , R2 = 5.2 k $\Omega$ , C1 = C2 = 1  $\mu$ F, C<sub>L</sub> = 50 pF, Vcc = 12V, Forward current gain of the transistor,  $\beta$  = 200. [5 x 4 = 20 Marks]



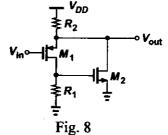
- (i) Find the values of  $R_E$  and  $R_C$  such that the operating point of the transistor is,  $I_{CQ} = 2.5 \text{mA}$  and  $V_{CEQ} = 4.5 \text{V}$ . Use these value of  $R_E$  and  $R_C$  for the subsequent parts of this question.
- (ii) Draw small signal equivalent circuit of the amplifier. Using the small signal equivalent circuit, derive the expression of transconductance of the amplifier.
- (iii) Find the values of voltage gain and the lower cutoff frequency of the amplifier.
- (iv) For an input signal of  $v_{in} = 1 + \sin(2000\pi t 180^{\circ})$  volts, neatly sketch (including d.c. level and the phase) the voltage waveforms at the base, emitter and collector nodes of the transistor.
- (v) How can we increase the gain of the amplifier? What is the value of the gain of the amplifier with your suggested modification?
- 5. Refer to the amplifier circuit shown in Fig. 7. Forward current gain of the two transistors in the circuit are,  $\beta_1 = 150$  and  $\beta_2 = 49$ . Given values of the circuit components are: R1 = 15.5 k $\Omega$ , R2 = 560  $\Omega$ , C1 = 1  $\mu$ F, C<sub>L</sub> = 100 pF, Vcc = 12V. [6 + 7 + 4 + 3 = 20 Marks]



(i) Find the value of  $R_B$  so that the d.c. voltage at the output node is 5.6V. With this value of  $R_B$ , find the operating points of the two transistors. Use this value of  $R_B$  for the subsequent parts of this question.

- (ii) Draw the small signal equivalent circuit of the given amplifier. Using the small signal equivalent circuit, derive the expression of voltage gain and output resistance of the amplifier.
- (iii) Find the values of the upper cutoff frequency and the voltage gain of the amplifier.
- (iv) Find the value of maximum swing of the output signal (sinusoidal) with which both the transistors remain in active region of operation.
- 6. Construct the small-signal model of the circuit in Fig. 8 where  $M_1$  and  $M_2$  are in saturation. Obtain  $V_{out}/V_{in}$  and the output impedance,  $R_{out}$ . [Hint: For  $R_{out}$  apply test voltage  $V_x$  at the output and find the current,  $I_x$ , flowing through the test voltage  $V_x$ .  $R_{out} = V_x/I_x$ .  $V_{in}$  should be an AC ground during this analysis.]

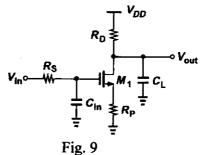
  [2+4+4 = 10 Marks]



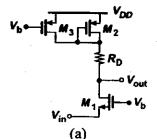
7. Obtain the transfer function  $\frac{v_{out}}{v_{in}}$  (s) for the circuit in Fig. 9.

[5+3+2=10 Marks]

- (a) by exact analysis i.e., by drawing the small signal model.
- (b) From the transfer function obtained in (a) identify the nodes and the corresponding poles.
- (c) Draw the corresponding Bode-plot for the transfer function obtained in (a). Annotate the poles as  $\omega_{p1}, \omega_{p2}, \cdots, \omega_{pN}$  and zeroes as  $\omega_{z1}, \omega_{z2}, \cdots, \omega_{zN}$ . Since the resistor and capacitor values are not given you are free to appropriately assign the order of the poles. For example, you can choose the order as  $\omega_{p1} < \omega_{p2} < \cdots < \omega_{pN}$  and  $\omega_{z1} < \omega_{z2} < \cdots < \omega_{zN}$ . The Bode plot should then be appropriately done.



8. Determine the voltage gain of the circuits given in Fig. 10 using the concept of  $G_m$  and  $R_{\text{out}}$ . Keep in mind that  $R_{\text{out}} = R_{\text{up}} || R_{\text{down}}$ . (Assume  $\lambda = 0$ ).



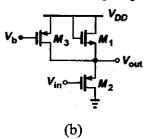


Fig. 10